CLAIMS

1. A ceramic substrate, for a semiconductor producing/examining device, having a conductor formed inside thereof or on the surface thereof,

wherein said ceramic substrate has been sintered such that a fractured section thereof exhibits intergranular fracture.

2. The ceramic substrate for a semiconductor producing/examining device according to claim 1,

wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10 μm.

3. The ceramic substrate for a semiconductor producing/examining device according to claim 1,

wherein an impurity element is locally distributed in boundaries of ceramic grains of said fractured section.

4. The ceramic substrate for a semiconductor producing/examining device according to claim 1,

wherein thermal conductivity of said ceramic substrate is 100 W/m·K or more.

5. The ceramic substrate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is constituted such that:

an impurity-existent area where an impurity element is locally distributed in triple points of crystal grains, and

an impurity element-nonexistent area where an impurity is not locally distributed in the triple points of the crystal grains,

coexist therein.